

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

NISHIMOTO et al

Serial No.: 08/897,839

Filed: July 21, 1997

For: STRESS-ADJUSTED INSULATING  
FILM FORMING METHOD,  
SEMICONDUCTOR DEVICE AND  
METHOD OF MANUFACTURING THE  
SAME

Group Art Unit: 2814

Examiner: K. Eaton

VIA FACSIMILE

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MAY 23 2000

TECHNOLOGY CENTER 2800

SUPPLEMENTAL AMENDMENT IN RESPONSE  
TO OFFICE ACTION OF FEBRUARY 3, 2000

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Supplemental to Applicants' response filed May 3, 2000,  
please amend the captioned application as follows:

IN THE SPECIFICATION:

Page 7, line 7, change "dyne/cm<sup>2</sup>" to read --dyne/cm--; and  
line 8, after "experiment" insert --, a value obtained  
by multiplying the stress in a layer (in dynes/cm<sup>2</sup>) by the  
thickness of that layer, and accumulated for all layers--.

Page 12, line 12, change "dyne/cm<sup>2</sup>" to read --dyne/cm--.

Page 13, line 12, change "dyne/cm<sup>2</sup>" to read --dyne/cm--.

Page 20, line 21, change "dyne/cm<sup>2</sup>" to read --dyne/cm--.

Page 21, line 19, change "dyne/cm<sup>2</sup>" to read --dyne/cm--; and  
line 21, change "dyne/cm<sup>2</sup>" to read --dyne/cm--.

NE  
Wrong  
page & line